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### Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

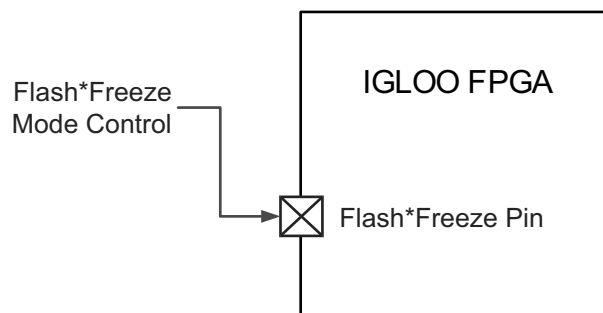
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	215
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	281-TFBGA, CSBGA
Supplier Device Package	281-CSP (10x10)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/agl600v5-csg281i">https://www.e-xfl.com/product-detail/microchip-technology/agl600v5-csg281i</a>

## Flash\*Freeze Technology

The IGLOO device has an ultra-low power static mode, called Flash\*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash\*Freeze technology enables the user to quickly (within 1  $\mu$ s) enter and exit Flash\*Freeze mode by activating the Flash\*Freeze pin while all power supplies are kept at their original values. In addition, I/Os and global I/Os can still be driven and can be toggling without impact on power consumption, clocks can still be driven or can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and states. I/O states are tristated during Flash\*Freeze mode or can be set to a certain state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL, and the device consumes as little as 5  $\mu$ W in this mode.

Flash\*Freeze technology allows the user to switch to active mode on demand, thus simplifying the power management of the device.

The Flash\*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. It is also possible to use the Flash\*Freeze pin as a regular I/O if Flash\*Freeze mode usage is not planned, which is advantageous because of the inherent low power static (as low as 12  $\mu$ W) and dynamic capabilities of the IGLOO device. Refer to Figure 1-3 for an illustration of entering/exiting Flash\*Freeze mode.



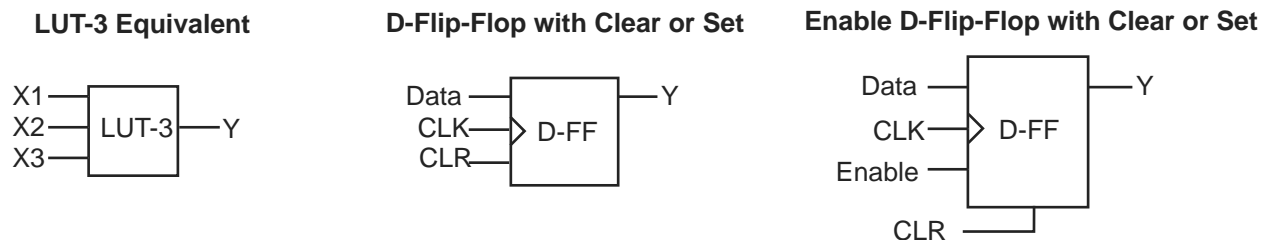
**Figure 1-3 • IGLOO Flash\*Freeze Mode**

## VersaTiles

The IGLOO core consists of VersaTiles, which have been enhanced beyond the ProASIC<sup>PLUS</sup>® core tiles. The IGLOO VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-4 for VersaTile configurations.



**Figure 1-4 • VersaTile Configurations**

## Temperature and Voltage Derating Factors

**Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$ )**  
For IGLOO V2 or V5 devices, 1.5 V DC Core Supply Voltage

Array Voltage VCC (V)	Junction Temperature ( $^\circ\text{C}$ )					
	$-40^\circ\text{C}$	$0^\circ\text{C}$	$25^\circ\text{C}$	$70^\circ\text{C}$	$85^\circ\text{C}$	$100^\circ\text{C}$
1.425	0.934	0.953	0.971	1.000	1.007	1.013
1.500	0.855	0.874	0.891	0.917	0.924	0.929
1.575	0.799	0.816	0.832	0.857	0.864	0.868

**Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.14\text{ V}$ )**  
For IGLOO V2, 1.2 V DC Core Supply Voltage

Array Voltage VCC (V)	Junction Temperature ( $^\circ\text{C}$ )					
	$-40^\circ\text{C}$	$0^\circ\text{C}$	$25^\circ\text{C}$	$70^\circ\text{C}$	$85^\circ\text{C}$	$100^\circ\text{C}$
1.14	0.967	0.978	0.991	1.000	1.006	1.010
1.20	0.864	0.874	0.885	0.894	0.899	0.902
1.26	0.794	0.803	0.814	0.821	0.827	0.830

## Calculating Power Dissipation

### Quiescent Supply Current

Quiescent supply current ( $I_{DD}$ ) calculation depends on multiple factors, including operating voltages ( $V_{CC}$ ,  $V_{CCI}$ , and  $V_{JTAG}$ ), operating temperature, system clock frequency, and power modes usage. Microsemi recommends using the PowerCalculator and SmartPower software estimation tools to evaluate the projected static and active power based on the user design, power mode usage, operating voltage, and temperature.

**Table 2-8 • Power Supply State per Mode**

Modes/power supplies	Power Supply Configurations				
	VCC	VCCPLL	VCCI	VJTAG	VPUMP
Flash*Freeze	On	On	On	On	On/off/floating
Sleep	Off	Off	On	Off	Off
Shutdown	Off	Off	Off	Off	Off
No Flash*Freeze	On	On	On	On	On/off/floating

Note: Off: Power supply level = 0 V

**Table 2-9 • Quiescent Supply Current ( $I_{DD}$ ) Characteristics, IGLOO Flash\*Freeze Mode\***

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
Typical ( $25^\circ\text{C}$ )	1.2 V	4	4	8	13	20	27	30	44	$\mu\text{A}$
	1.5 V	6	6	10	18	34	51	72	127	$\mu\text{A}$

Note: \* $I_{DD}$  includes VCC, VPUMP, VCCI, VCCPLL, and VMV currents. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

## Power Consumption of Various Internal Resources

**Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices**  
For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage

Parameter	Definition	Device Specific Dynamic Power ( $\mu\text{W}/\text{MHz}$ )							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	7.778	6.221	6.082	4.460	4.446	2.736	0.000	0.000
PAC2	Clock contribution of a Global Spine	4.334	3.512	2.759	2.718	1.753	1.971	3.483	3.483
PAC3	Clock contribution of a VersaTile row	1.379	1.445	1.377	1.483	1.467	1.503	1.472	1.472
PAC4	Clock contribution of a VersaTile used as a sequential module	0.151	0.149	0.151	0.149	0.149	0.151	0.146	0.146
PAC5	First contribution of a VersaTile used as a sequential module	0.057							
PAC6	Second contribution of a VersaTile used as a sequential module	0.207							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.276	0.262	0.279	0.277	0.280	0.300	0.281	0.273
PAC8	Average contribution of a routing net	1.161	1.147	1.193	1.273	1.076	1.088	1.134	1.153
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.70							

*Note:* For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

**Table 2-21 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices  
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power ( $\mu\text{W}/\text{MHz}$ )							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	4.978	3.982	3.892	2.854	2.845	1.751	0.000	0.000
PAC2	Clock contribution of a Global Spine	2.773	2.248	1.765	1.740	1.122	1.261	2.229	2.229
PAC3	Clock contribution of a VersaTile row	0.883	0.924	0.881	0.949	0.939	0.962	0.942	0.942
PAC4	Clock contribution of a VersaTile used as a sequential module	0.096	0.095	0.096	0.095	0.095	0.096	0.094	0.094
PAC5	First contribution of a VersaTile used as a sequential module	0.045							
PAC6	Second contribution of a VersaTile used as a sequential module	0.186							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.158	0.149	0.158	0.157	0.160	0.170	0.160	0.155
PAC8	Average contribution of a routing net	0.756	0.729	0.753	0.817	0.678	0.692	0.738	0.721
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.10							

*Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.*

**Combinatorial Cells Contribution— $P_{C-CELL}$** 

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$$

$N_{C-CELL}$  is the number of VersaTiles used as combinatorial modules in the design.

$\alpha_1$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**Routing Net Contribution— $P_{NET}$** 

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$$

$N_{S-CELL}$  is the number of VersaTiles used as sequential modules in the design.

$N_{C-CELL}$  is the number of VersaTiles used as combinatorial modules in the design.

$\alpha_1$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**I/O Input Buffer Contribution— $P_{INPUTS}$** 

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$$

$N_{INPUTS}$  is the number of I/O input buffers used in the design.

$\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**I/O Output Buffer Contribution— $P_{OUTPUTS}$** 

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$$

$N_{OUTPUTS}$  is the number of I/O output buffers used in the design.

$\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

$\beta_1$  is the I/O buffer enable rate—guidelines are provided in Table 2-24 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**RAM Contribution— $P_{MEMORY}$** 

$$P_{MEMORY} = P_{AC11} * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + P_{AC12} * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

$N_{BLOCKS}$  is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$  is the memory read clock frequency.

$\beta_2$  is the RAM enable rate for read operations.

$F_{WRITE-CLOCK}$  is the memory write clock frequency.

$\beta_3$  is the RAM enable rate for write operations—guidelines are provided in Table 2-24 on page 2-19.

**PLL Contribution— $P_{PLL}$** 

$$P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$$

$F_{CLKOUT}$  is the output clock frequency.<sup>†</sup>

<sup>†</sup> If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ( $P_{AC13} * F_{CLKOUT}$  product) to the total PLL contribution.

**Table 2-35 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case**  
**Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ , Worst-Case  $V_{CCI}$  (per standard)**  
**Applicable to Standard Plus I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup> (mA)	Slew Rate	Capacitive Load (pF)	External Resistor ( $\Omega$ )	$t_{\text{BOUT}}$ (ns)	$t_{\text{BP}}$ (ns)	$t_{\text{BIN}}$ (ns)	$t_{\text{PY}}$ (ns)	$t_{\text{EOUT}}$ (ns)	$t_{\text{ZL}}$ (ns)	$t_{\text{ZH}}$ (ns)	$t_{\text{LZ}}$ (ns)	$t_{\text{HZ}}$ (ns)	$t_{\text{ZLS}}$ (ns)	$t_{\text{ZHS}}$ (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 $\mu\text{A}$	12	High	5	–	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns
2.5 V LVCMOS	12 mA	12	High	5	–	1.55	2.29	0.26	1.19	1.10	2.32	1.94	2.94	3.52	8.10	7.73	ns
1.8 V LVCMOS	8 mA	8	High	5	–	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
1.5 V LVCMOS	4 mA	4	High	5	–	1.55	2.68	0.26	1.27	1.10	2.72	2.39	3.07	3.37	8.50	8.18	ns
1.2 V LVCMOS	2 mA	2	High	5	–	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns
1.2 V LVCMOS Wide Range <sup>3</sup>	100 $\mu\text{A}$	2	High	5	–	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns
3.3 V PCI	Per PCI spec	–	High	10	25 <sup>2</sup>	1.55	2.53	0.26	0.84	1.10	2.57	1.98	2.93	3.64	8.35	7.76	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 <sup>2</sup>	1.55	2.53	0.25	0.85	1.10	2.57	1.98	2.93	3.64	8.35	7.76	ns

## Notes:

1. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\text{ }\mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.
5. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

## Timing Characteristics

Applies to 1.5 V DC Core Voltage

**Table 2-67 • 3.3 V LVC MOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V**  
**Applicable to Advanced Banks**

Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
100 $\mu\text{A}$	2 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 $\mu\text{A}$	4 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 $\mu\text{A}$	6 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 $\mu\text{A}$	8 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 $\mu\text{A}$	12 mA	Std.	0.97	4.69	0.18	1.19	0.66	4.71	4.25	3.80	4.10	8.31	7.85	ns
100 $\mu\text{A}$	16 mA	Std.	0.97	4.46	0.18	1.19	0.66	4.48	4.11	3.86	4.21	8.07	7.71	ns
100 $\mu\text{A}$	24 mA	Std.	0.97	4.34	0.18	1.19	0.66	4.36	4.14	3.93	4.64	7.95	7.74	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**Table 2-68 • 3.3 V LVC MOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V**  
**Applicable to Advanced Banks**

Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
100 $\mu\text{A}$	2 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 $\mu\text{A}$	4 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 $\mu\text{A}$	6 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 $\mu\text{A}$	8 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 $\mu\text{A}$	12 mA	Std.	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
100 $\mu\text{A}$	16 mA	Std.	0.97	2.87	0.18	1.19	0.66	2.89	2.22	3.86	4.41	6.49	5.82	ns
100 $\mu\text{A}$	24 mA	Std.	0.97	2.90	0.18	1.19	0.66	2.92	2.16	3.94	4.86	6.51	5.75	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
2. Software default selection highlighted in gray.
3. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.



**Table 2-138 • Minimum and Maximum DC Input and Output Levels for LVCMOS 1.2 V Wide Range**  
Applicable to Standard Plus I/O Banks

1.2 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>2</sup>	IIH <sup>3</sup>
Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>4</sup>	Max. mA <sup>4</sup>	μA <sup>5</sup>	μA <sup>5</sup>
100 μA	2mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

1. The minimum drive strength for the default LVCMOS 1.2 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$ .
3. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$ . Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

**Table 2-139 • Minimum and Maximum DC Input and Output Levels for LVCMOS 1.2 V Wide Range**  
Applicable to Standard I/O Banks

1.2 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>2</sup>	IIH <sup>3</sup>
Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>4</sup>	Max. mA <sup>4</sup>	μA <sup>5</sup>	μA <sup>5</sup>
100 μA	1 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

1. The minimum drive strength for the default LVCMOS 1.2 V software configuration when run in wide range is  $\pm 100 \mu\text{A}$ . The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$ .
3. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$ . Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

**Table 2-140 • 1.2 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C <sub>LOAD</sub> (pF)
0	1.2	0.6	5

Note: \*Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

**Timing Characteristics**

Refer to LVCMOS 1.2 V (normal range) "Timing Characteristics" on page 2-75 for worst-case timing.

### 3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

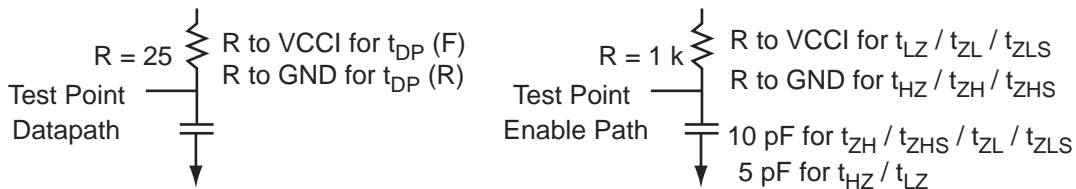
**Table 2-141 • Minimum and Maximum DC Input and Output Levels**  
Applicable to Advanced and Standard Plus I/Os

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>1</sup>	Max. mA <sup>1</sup>	μA <sup>2</sup>	μA <sup>2</sup>
Per PCI specification	Per PCI curves										10	10

Notes:

1. Currents are measured at 100°C junction temperature and maximum voltage.
2. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-12.



**Figure 2-12 • AC Loading**

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-142.

**Table 2-142 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C <sub>LOAD</sub> (pF)
0	3.3	0.285 * VCCI for t <sub>DP(R)</sub> 0.615 * VCCI for t <sub>DP(F)</sub>	10

Note: \*Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

### Timing Characteristics

#### 1.5 V DC Core Voltage

**Table 2-143 • 3.3 V PCI/PCI-X**

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V  
Applicable to Advanced I/O Banks

Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
Std.	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**Table 2-144 • 3.3 V PCI/PCI-X**

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V  
Applicable to Standard Plus I/O Banks

Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
Std.	0.97	1.97	0.19	0.70	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

## 1.2 V DC Core Voltage

Table 2-158 • Input Data Register Propagation Delays

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ 

Parameter	Description	Std.	Units
$t_{\text{ICLKQ}}$	Clock-to-Q of the Input Data Register	0.68	ns
$t_{\text{ISUD}}$	Data Setup Time for the Input Data Register	0.97	ns
$t_{\text{IHD}}$	Data Hold Time for the Input Data Register	0.00	ns
$t_{\text{ISUE}}$	Enable Setup Time for the Input Data Register	1.02	ns
$t_{\text{IHE}}$	Enable Hold Time for the Input Data Register	0.00	ns
$t_{\text{ICLR2Q}}$	Asynchronous Clear-to-Q of the Input Data Register	1.19	ns
$t_{\text{IPRE2Q}}$	Asynchronous Preset-to-Q of the Input Data Register	1.19	ns
$t_{\text{IREMCLR}}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{\text{IRECCLR}}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{\text{IREMPRE}}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{\text{IRECPRE}}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
$t_{\text{IWCLR}}$	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{\text{IWPRE}}$	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{\text{ICKMPWH}}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{\text{ICKMPWL}}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

## Output Register

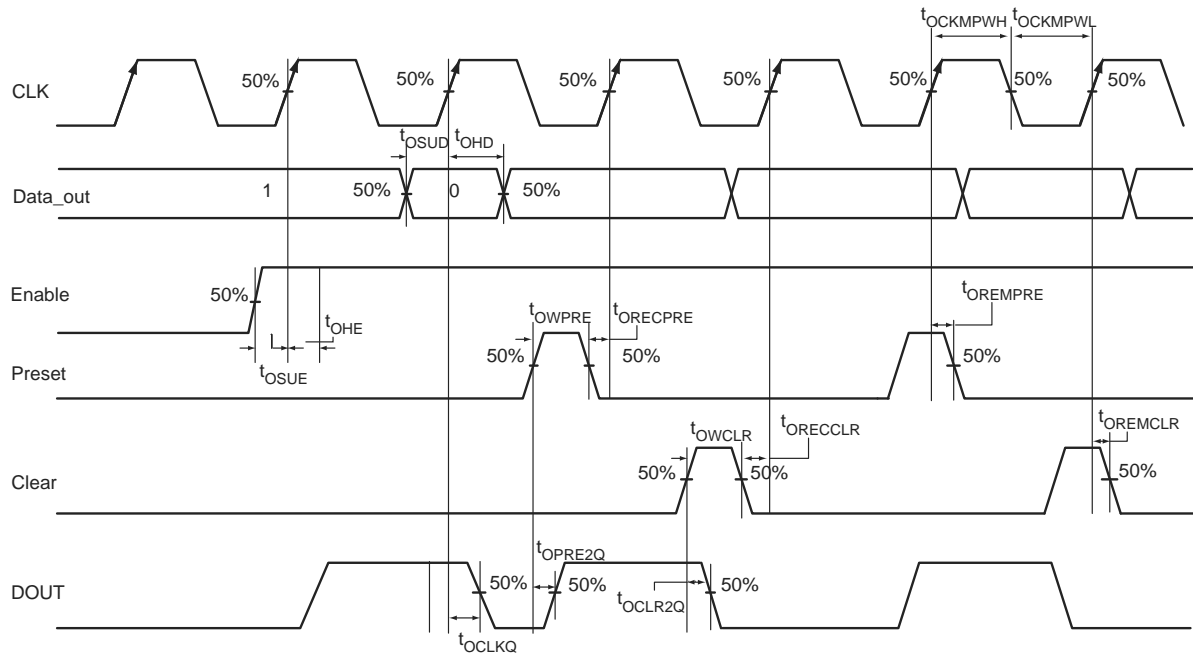
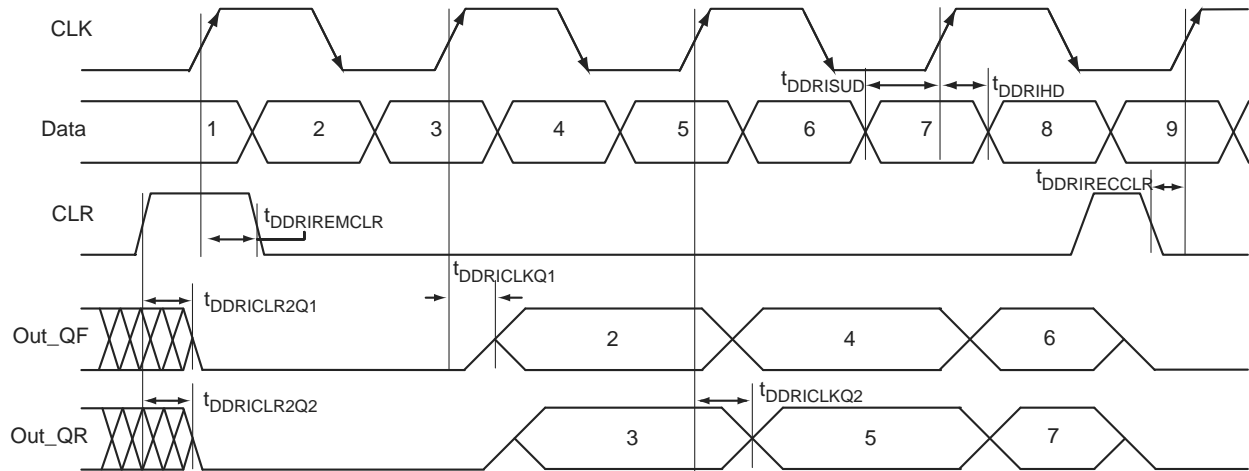


Figure 2-19 • Output Register Timing Diagram



**Figure 2-22 • Input DDR Timing Diagram**

**Timing Characteristics**

**1.5 V DC Core Voltage**

**Table 2-164 • Input DDR Propagation Delays**

**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.	Units
$t_{\text{DDRCLKQ1}}$	Clock-to-Out Out_QR for Input DDR	0.48	ns
$t_{\text{DDRCLKQ2}}$	Clock-to-Out Out_QF for Input DDR	0.65	ns
$t_{\text{DDRISUD1}}$	Data Setup for Input DDR (negedge)	0.50	ns
$t_{\text{DDRISUD2}}$	Data Setup for Input DDR (posedge)	0.40	ns
$t_{\text{DDRHD1}}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{\text{DDRHD2}}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{\text{DDRCLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.82	ns
$t_{\text{DDRCLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.98	ns
$t_{\text{DDRREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{\text{DDRRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.23	ns
$t_{\text{DDRWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
$F_{\text{DDRIMAX}}$	Maximum Frequency for Input DDR	250.00	MHz

*Note:* For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

## 1.2 V DC Core Voltage

Table 2-165 • Input DDR Propagation Delays

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ 

Parameter	Description	Std.	Units
$t_{\text{DDRICKQ1}}$	Clock-to-Out Out_QR for Input DDR	0.76	ns
$t_{\text{DDRICKQ2}}$	Clock-to-Out Out_QF for Input DDR	0.94	ns
$t_{\text{DDRISUD1}}$	Data Setup for Input DDR (negedge)	0.93	ns
$t_{\text{DDRISUD2}}$	Data Setup for Input DDR (posedge)	0.84	ns
$t_{\text{DDRILD1}}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{\text{DDRILD2}}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{\text{DDRICLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	1.23	ns
$t_{\text{DDRICLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
$t_{\text{DDRIREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{\text{DDRIRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
$t_{\text{DDRIWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
$F_{\text{DDRIMAX}}$	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Table 2-175 • AGL060 Global Resource****Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ ,  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{\text{RCKL}}$	Input Low Delay for Global Clock	1.33	1.55	ns
$t_{\text{RCKH}}$	Input High Delay for Global Clock	1.35	1.62	ns
$t_{\text{RCKMPWH}}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{\text{RCKMPWL}}$	Minimum Pulse Width Low for Global Clock	1.15		ns
$t_{\text{RCKSW}}$	Maximum Skew for Global Clock		0.27	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**Table 2-176 • AGL125 Global Resource****Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ ,  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{\text{RCKL}}$	Input Low Delay for Global Clock	1.36	1.71	ns
$t_{\text{RCKH}}$	Input High Delay for Global Clock	1.39	1.82	ns
$t_{\text{RCKMPWH}}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{\text{RCKMPWL}}$	Minimum Pulse Width Low for Global Clock	1.15		ns
$t_{\text{RCKSW}}$	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

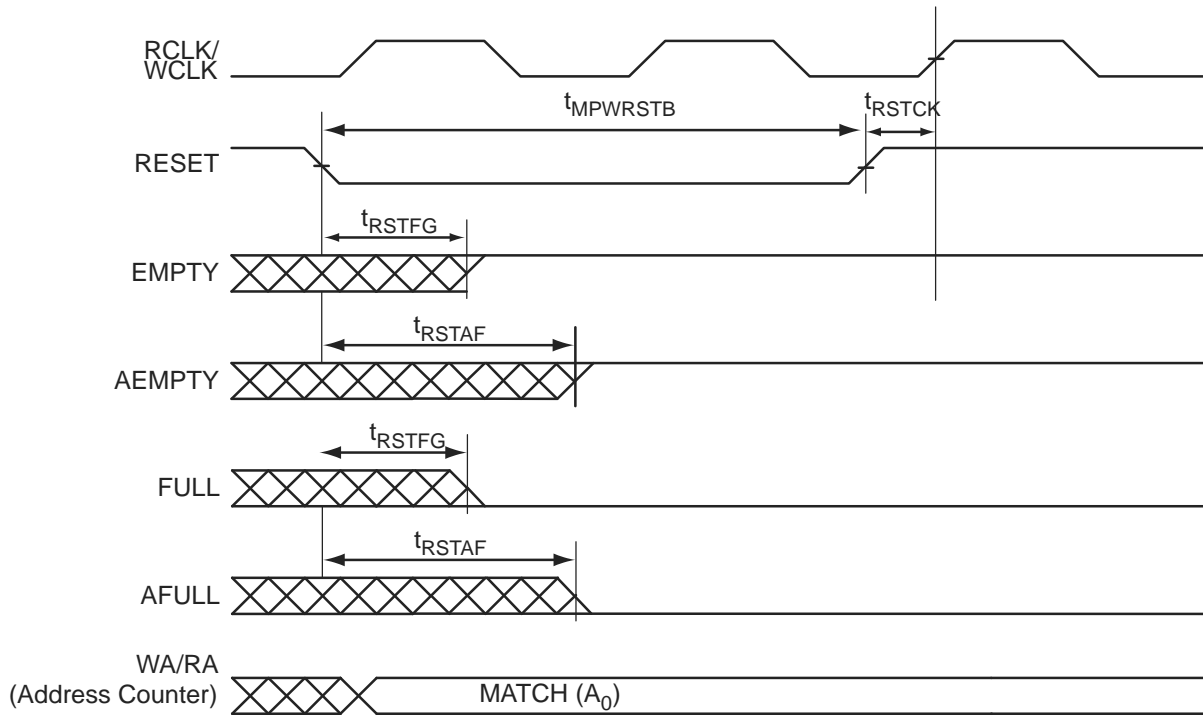


Figure 2-40 • FIFO Reset

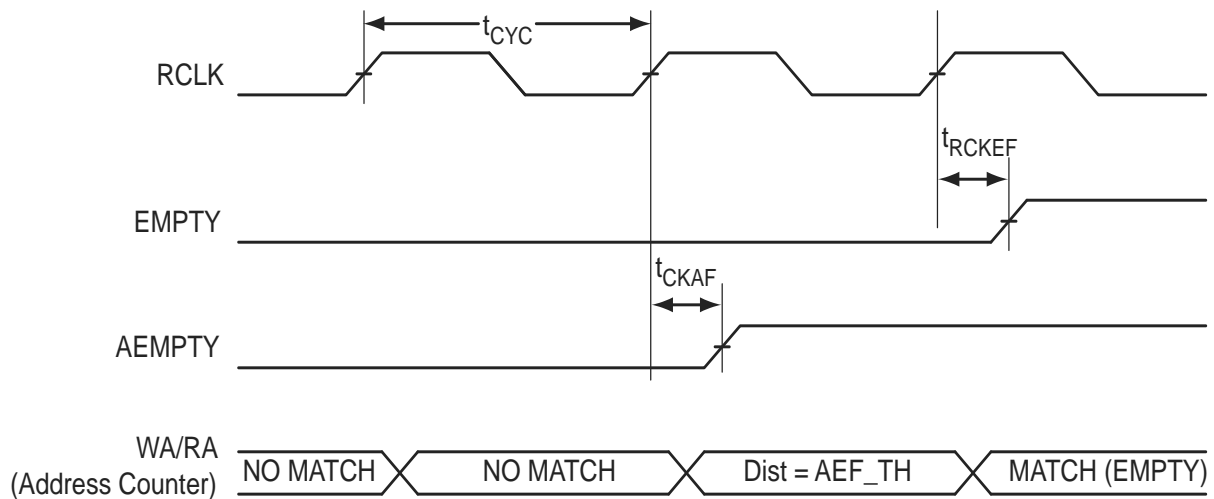
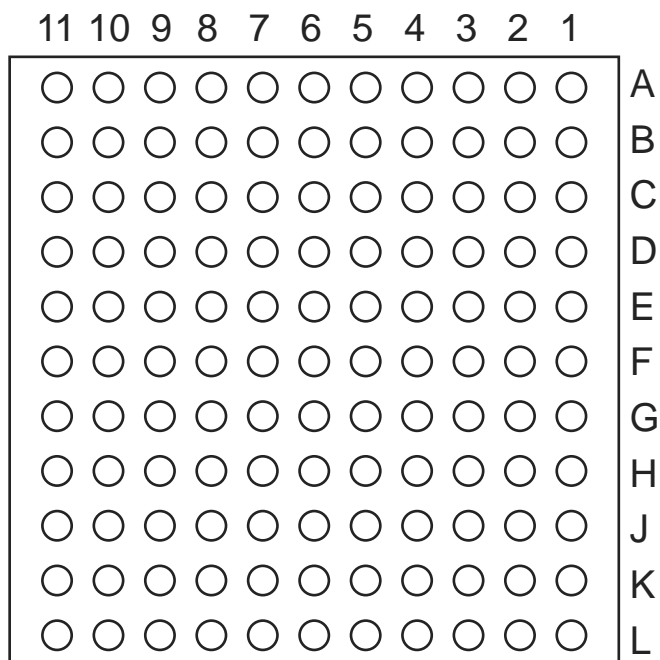


Figure 2-41 • FIFO EMPTY Flag and AEMPTY Flag Assertion

## CS121

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*Note:* This is the bottom view of the package.

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### **Note**

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.



CS196	
Pin Number	AGL125 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO09RSB0
A6	IO15RSB0
A7	IO18RSB0
A8	IO22RSB0
A9	IO27RSB0
A10	GBC0/IO35RSB0
A11	GBB0/IO37RSB0
A12	GBB1/IO38RSB0
A13	GBA1/IO40RSB0
A14	GND
B1	VCCIB1
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO16RSB0
B7	IO20RSB0
B8	IO24RSB0
B9	IO28RSB0
B10	GND
B11	GBC1/IO36RSB0
B12	GBA0/IO39RSB0
B13	GBA2/IO41RSB0
B14	GBB2/IO43RSB0
C1	GAC2/IO128RSB1
C2	GAB2/IO130RSB1
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO14RSB0
C7	VCCIB0
C8	NC

CS196	
Pin Number	AGL125 Function
C9	IO23RSB0
C10	IO29RSB0
C11	VCCIB0
C12	IO42RSB0
C13	GNDQ
C14	IO44RSB0
D1	IO127RSB1
D2	IO129RSB1
D3	GAA2/IO132RSB1
D4	IO126RSB1
D5	IO06RSB0
D6	IO13RSB0
D7	IO19RSB0
D8	IO21RSB0
D9	IO26RSB0
D10	IO31RSB0
D11	IO30RSB0
D12	VMV0
D13	IO46RSB0
D14	GBC2/IO45RSB0
E1	IO125RSB1
E2	GND
E3	IO131RSB1
E4	VCCIB1
E5	NC
E6	IO08RSB0
E7	IO17RSB0
E8	IO12RSB0
E9	IO11RSB0
E10	NC
E11	VCCIB0
E12	IO32RSB0
E13	GND
E14	IO34RSB0
F1	IO124RSB1
F2	IO114RSB1

CS196	
Pin Number	AGL125 Function
F3	IO113RSB1
F4	IO112RSB1
F5	IO111RSB1
F6	NC
F7	VCC
F8	VCC
F9	NC
F10	IO07RSB0
F11	IO25RSB0
F12	IO10RSB0
F13	IO33RSB0
F14	IO47RSB0
G1	GFB1/IO121RSB1
G2	GFA0/IO119RSB1
G3	GFA2/IO117RSB1
G4	VCOMPLF
G5	GFC0/IO122RSB1
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO52RSB0
G11	GCB1/IO53RSB0
G12	GCA0/IO56RSB0
G13	IO48RSB0
G14	GCC2/IO59RSB0
H1	GFB0/IO120RSB1
H2	GFA1/IO118RSB1
H3	VCCPLF
H4	GFB2/IO116RSB1
H5	GFC1/IO123RSB1
H6	VCC
H7	GND
H8	GND
H9	VCC
H10	GCC1/IO51RSB0

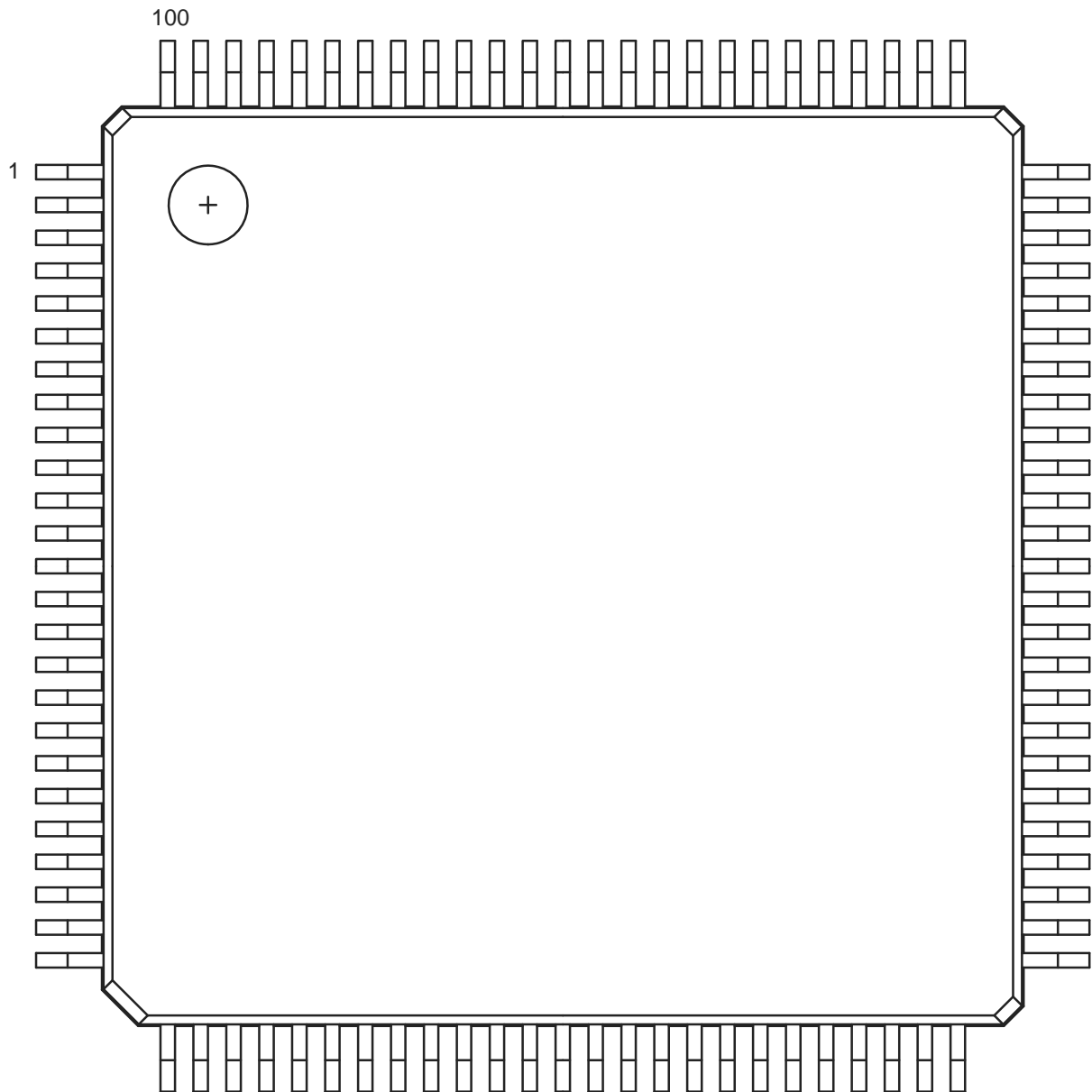
CS196	
Pin Number	AGL400 Function
H10	GCC1/IO67PDB1
H11	GCB0/IO68NDB1
H12	GCA1/IO69PDB1
H13	IO70NDB1
H14	GCA2/IO70PDB1
J1	GFC2/IO142PDB3
J2	IO141PPB3
J3	IO143NPB3
J4	IO140PDB3
J5	IO140NDB3
J6	IO109RSB2
J7	VCC
J8	VCC
J9	IO84RSB2
J10	IO75PDB1
J11	GCB2/IO71PDB1
J12	IO71NDB1
J13	GDC1/IO77UDB1
J14	GDC0/IO77VDB1
K1	IO142NDB3
K2	GND
K3	IO141NPB3
K4	VCCIB3
K5	IO138PPB3
K6	IO125RSB2
K7	IO110RSB2
K8	IO98RSB2
K9	IO104RSB2
K10	IO75NDB1
K11	VCCIB1
K12	GDA1/IO79UPB1
K13	GND
K14	GDB1/IO78UDB1
L1	GEB1/IO136PDB3
L2	GEC1/IO137PDB3
L3	GEC0/IO137NDB3

CS196	
Pin Number	AGL400 Function
L4	IO138NPB3
L5	IO122RSB2
L6	IO128RSB2
L7	IO101RSB2
L8	IO88RSB2
L9	IO86RSB2
L10	IO94RSB2
L11	VPUMP
L12	VJTAG
L13	GDA0/IO79VPB1
L14	GDB0/IO78VDB1
M1	GEB0/IO136NDB3
M2	GEA1/IO135PPB3
M3	GNDQ
M4	VCCIB2
M5	IO120RSB2
M6	IO119RSB2
M7	IO112RSB2
M8	VCCIB2
M9	IO89RSB2
M10	GDB2/IO81RSB2
M11	VCCIB2
M12	VMV2
M12	VMV2
M13	TRST
M14	VCCIB1
N1	GEA0/IO135NPB3
N2	VMV3
N3	GEC2/IO132RSB2
N4	IO130RSB2
N5	GND
N6	IO117RSB2
N7	IO106RSB2
N8	IO100RSB2
N9	IO92RSB2
N10	GND

CS196	
Pin Number	AGL400 Function
N11	TCK
N12	TDI
N13	GNDQ
N14	TDO
P1	GND
P2	GEA2/IO134RSB2
P3	FF/GEB2/IO133RSB2
P4	IO123RSB2
P5	IO116RSB2
P6	IO114RSB2
P7	IO107RSB2
P8	IO103RSB2
P9	IO95RSB2
P10	IO91RSB2
P11	GDC2/IO82RSB2
P12	GDA2/IO80RSB2
P13	TMS
P14	GND

## VQ100

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*Note:* This is the top view of the package.

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### **Note**

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

<b>FG144</b>	
<b>Pin Number</b>	<b>AGL400 Function</b>
K1	GEB0/IO136NDB3
K2	GEA1/IO135PDB3
K3	GEA0/IO135NDB3
K4	GEA2/IO134RSB2
K5	IO127RSB2
K6	IO121RSB2
K7	GND
K8	IO104RSB2
K9	GDC2/IO82RSB2
K10	GND
K11	GDA0/IO79VDB1
K12	GDB0/IO78VDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO133RSB2
L4	IO128RSB2
L5	VCCIB2
L6	IO119RSB2
L7	IO114RSB2
L8	IO110RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO132RSB2
M3	IO129RSB2
M4	IO126RSB2
M5	IO124RSB2
M6	IO122RSB2
M7	IO117RSB2
M8	IO115RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

Revision / Version	Changes	Page
Advance v0.4 (September 2007)	Cortex-M1 device information was added to Table 1 • IGLOO Product Family, the "I/Os Per Package1" table, "IGLOO Ordering Information", and Temperature Grade Offerings.	i, ii, iii, iv
	The number of single-ended I/Os for the CS81 package for AGL030 was updated to 66 in the "I/Os Per Package1" table.	ii
	The "Power Conservation Techniques" section was updated to recommend that unused I/O signals be left floating.	2-51
Advance v0.3 (August 2007)	In Table 1 • IGLOO Product Family, the CS81 package was added for AGL030. The CS196 was replaced by the CS121 for AGL060. Table note 3 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	i
	The CS81 and CS121 packages were added to the "I/Os Per Package1" table. The number of single-ended I/Os was removed for the CS196 package in AGL060. Table note 6 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	ii
	The CS81 and CS121 packages were added to the Temperature Grade Offerings table. The temperature grade offerings were removed for the CS196 package in AGL060. Table note 3 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	iv
	The CS81 and CS121 packages were added to Table 2-31 • Flash*Freeze Pin Location in IGLOO Family Packages (device-independent).	2-61
Advance v0.2	The words "ambient temperature" were added to the temperature range in the "IGLOO Ordering Information", Temperature Grade Offerings, and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The $T_J$ parameter in Table 3-2 • Recommended Operating Conditions was changed to $T_A$ , ambient temperature, and table notes 4–6 were added.	3-2